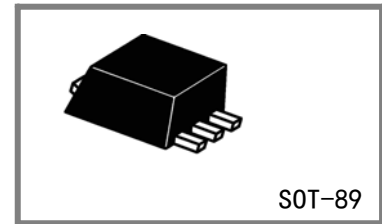
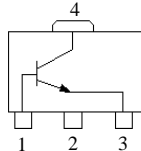


NPN-General use transistor

1W 1A 80V

**Applications:** Can be used for switching and amplifying in various electrical and electronic equipments.

**Circuit:**



MARKING

CY

### Max ratings

Parameters	Symbol	Rating	Unit
Collector-emitter voltage ( $I_B=0$ )	$V_{CEO}$	80	V
Collector-base voltage ( $I_E=0$ )	$V_{CBO}$	100	V
Emitter - base voltage ( $I_C=0$ )	$V_{EBO}$	5	V
Collector current	$I_C$	1	A
Total power dissipation ( $T_A=25^\circ\text{C}$ )*	$P_{tot}$	1	W
Max junction temperature	$T_{jm}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

\* mounted on printed circuit board.

### Characteristics (Unless otherwise specified, $T_A=25^\circ\text{C}$ )

Parameters	symbol	Test condition	min	typ	max	unit
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$ , $I_B=0$	80	—	—	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	100	—	—	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	5	—	—	V
Forward current transfer ratio <sup>1)</sup>	$h_{FE}$	$V_{CE}=2\text{V}$ ; $I_C=150\text{mA}$	120	—	240	—
Collector-base cutoff current	$I_{CBO}$	$V_{CB}=30\text{V}$ , $I_E=0$	—	—	100	nA
Collector-emitter saturation voltage <sup>1)</sup>	$V_{CE(sat)}$	$I_C=500\text{mA}$ , $I_B=50\text{mA}$	—	—	0.5	V
Transition frequency	$f_T$	$I_C=10\text{mA}$ , $V_{CE}=5\text{V}$ , $f=100\text{MHz}$	—	130	—	MHz

<sup>1)</sup> pulse method:  $t_w:300\mu\text{s}$ , duty ratio  $\leq 2\%$ .

## Typical curve

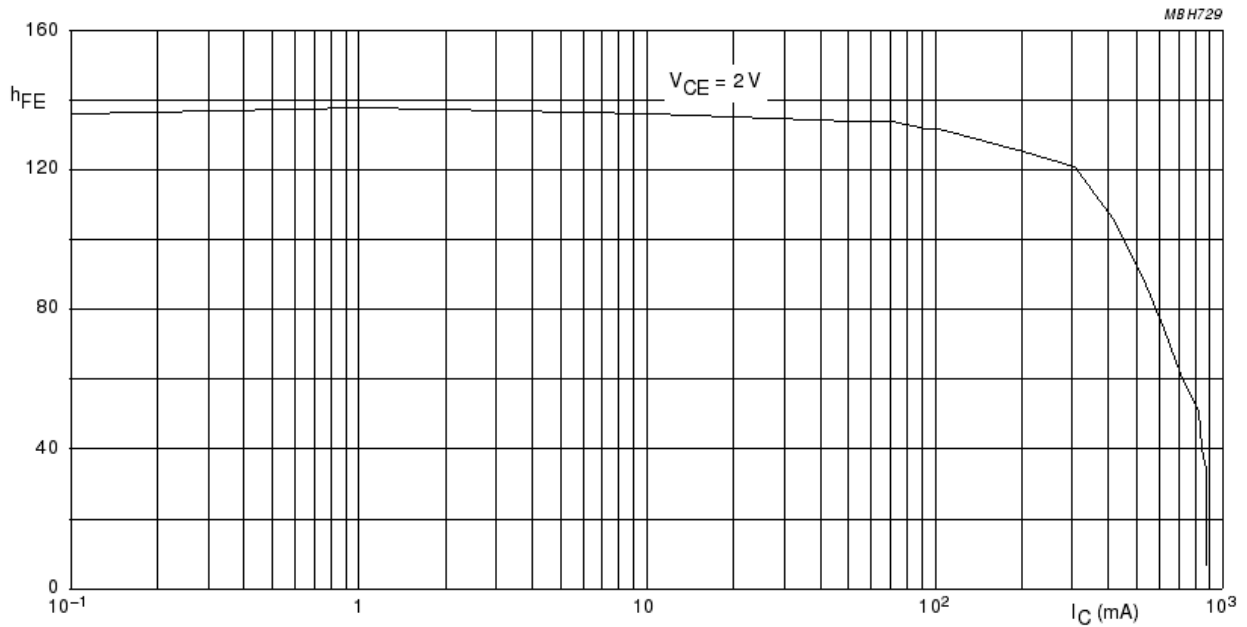
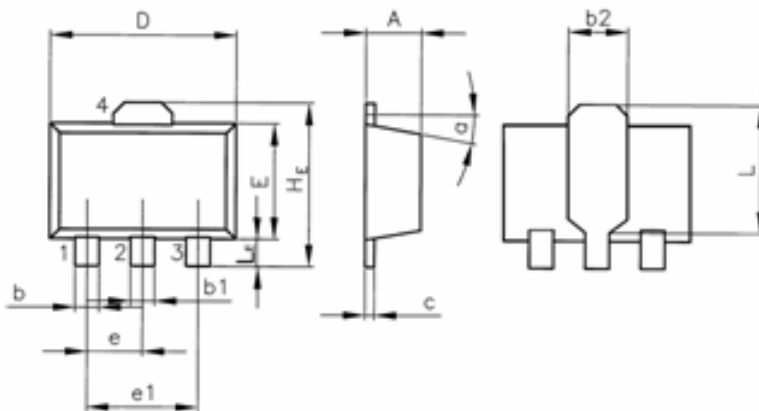


Fig.1 DC current gain; typical values.

## Outline dimensions

unit: mm



尺寸 符号	SOT-89		
	min	type	max
A	1.4		1.6
b	0.35		0.55
b1	0.4		0.65
b2		1.6	
c	0.35		0.45
D	4.4		4.6
E	2.35		2.55
e		1.5	
e1		3	
HE		4.15	
L		2.7	
LE		1.0	
a		5 $\phi$	

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)